NSN 5961-01-362-5666

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-362-5666 **Inclosure Material:** Glass **Overall Length:** Between 0.189 inches and 0.205 inches **Overall Diameter:** Between 0.094 inches and 0.105 inches **Function For Which Designed:** Microwave Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-213 **Mounting Method: Terminal Features Provided:** Burn in and hermetically sealed case and electrostatic sensitive **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 45.0 working peak reverse voltage **Current Rating Per Characteristic:** 1.00 amperes forward current, average absolute and 25.00 amperes forward current, average preset **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure:** Demilitarization: No Fiig: